HGW105N15M P-1

150V N-Ch Power MOSFET

V_{DS}		150	V
$R_{DS(on),typ}$	TO-262	8.8	mΩ
$I_{D\ (Sillicon\ Limited)}$		120	A

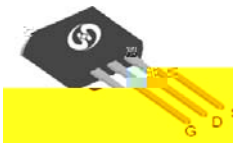
Feature

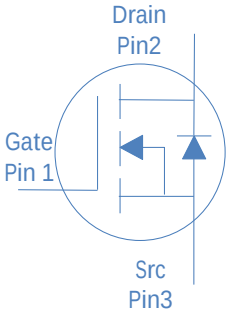
- High Speed Power Smooth Switching
- Enhanced Body diode dv/dt capability
- Enhanced Avalanche Ruggedness
- 100% UIS Tested, 100% Rg Tested
- Lead Free

Application

- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- Power Tools
- UPS
- Motor Control

TO-262





Part Number	Package	Marking
HGW105N15M	TO-262	GW105N15M

Absolute Maximum Ratings at T_j=25 (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_C=25	120	A
		T_C=100	85	
Drain to Source Voltage	V_{DS}	-	150	V
Gate to Source Voltage	V_{GS}	-	±20	V
Pulsed Drain Current	I_{DM}	-	400	A
Avalanche Energy, Single Pulse	E_{AS}	L=0.4mH, T_C=25	845	mJ
Power Dissipation	P_D	T_C=25	333	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to175	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{\Theta JC}$	0.45	/W
Thermal Resistance Junction-Ambient	$R_{\Theta JA}$	60	/W

Electrical Characteristics at T_j=25 (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	150	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}=V_{DS}, I_D=250μA	2	3	4	
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS}=0V, V_{DS}=150V, T_j=25	-	-	1	μA
		V_{GS}=0V, V_{DS}=150V, T_j=100	-	-	100	
Gate to Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain to Source on Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=20A TO-262	-	8.8	10.5	mΩ
Transconductance	g_{fs}	V_{DS}=5V, I_D=20A	-	90	-	S
Gate Resistance	R_G	V_{GS}=0V, V_{DS} Open, f=1MHz	-	0.7	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=75V, f=1MHz	-	4800	-	pF
Output Capacitance	C_{oss}		-	350	-	
Reverse Transfer Capacitance	C_{rss}		-	95	-	
Total Gate Charge	Q_g	V_{DD}=75V, I_D=20A, V_{GS}=10V	-	74	-	nC
Gate to Source Charge	Q_{gs}		-	15	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	28	-	
Turn on Delay Time	$t_{d(on)}$	V_{DD}=75V, I_D=20A, V_{GS}=10V, R_G=10Ω,	-	20	-	ns
Rise time	t_r		-	58	-	
Turn off Delay Time	$t_{d(off)}$		-	32	-	
Fall Time	t_f		-	31	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_F=20A	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R=75V, I_F=30A, dI_F/dt=100A/μs	-	120	-	ns
Reverse Recovery Charge	Q_{rr}		-	380	-	nC

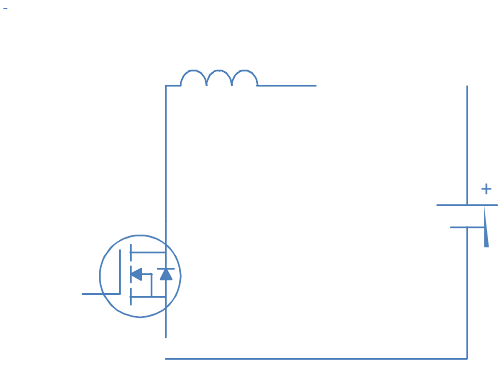
Fig 1. Typi

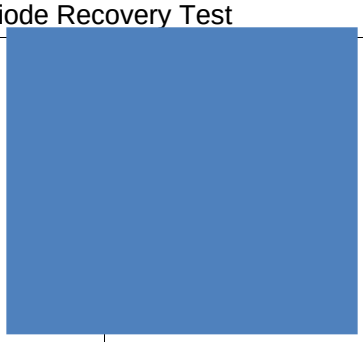
Figure 3. O

Figure 5. Typ

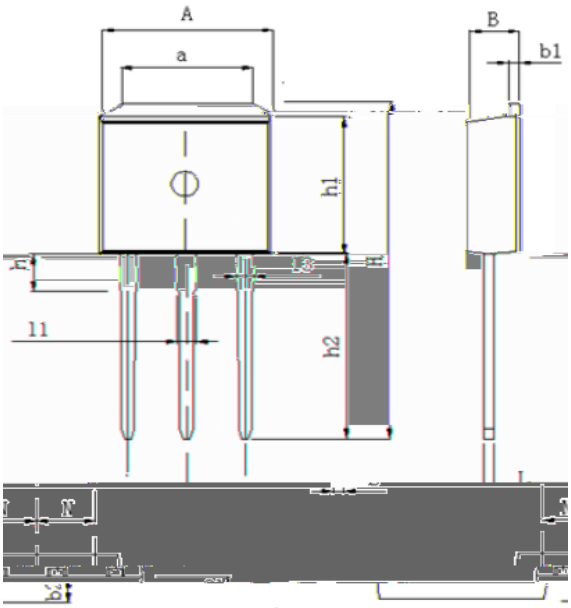
Inductive switching Test	

Gate Charge Test	

Uclamped Inductive Switching (UIS) Test	
	

Diode Recovery Test	
	

TO-262, 3 leads



Unit: mm

DIM	MILLIMETERS
A	9.98±0.2
a	7.4±0.4
B	4.5±0.2
b1	1.3±0.05
b2	2.4±0.2
H	23.9±0.3
h	3.1±0.2
h1	9.16±0.2
h2	13.2±0.2
L	0.5±0.1
l1	1.3±0.1
l2	0.8±0.1
N	2.45±0.1